							-			Code No.: 13404	O 3
VA), HYDERABAD y/June-2018	
				Ele	etron	ic Ma	aterials &	Dev	vices		
Tim	e: 3 hour		Answ	er ALL	quest	ions ir	n Part-A and	d any	FIVE fro	Max. Marks: 76 m Part-B	U
					Part-A	4 (10	\times 2 = 20 Me	arks)			
							emiconduct				
					-		on Voltage				
	rectifier	operat	ing at	a frequ	ency c	f 50H		-		onnected to a full wave $\frac{1}{2}$ for a load of 500Ω .	
	Define	-	_	_							
	List the					cuit.					
7.	Draw th	e h-par	amete	r mode	el for C	E BJ	Γ amplifier.				
8.	What is	intrins	ic star	doff ra	tio in	a UJT	?				
9.	Explain				_						
10.	A JFET	has a c	lrain c	urrent	of 15m	A. If I	I_{DSS} and V_p a	are 5n	mA and 5V	respectively, find V _{GS} .	
					Part-	B (5 >	\times 10 = 50 M	(arks)		
11.	a) Defi	ne and	derive	an exp	oressio	n for	diffusion ca	pacita	ance of a d	liode.	[
							Silicon PN V forward bi		de is 1µA	at room temperature.	1
12.	ripp	le facto	r, TUI	F and e	fficien	cy.				former and find its PIV,	
	b) Expl Dioc		h ener	gy ban	d diag	rams t	he operatior	and	the V-I cha	aracteristics of a Tunnel	
13.	three	e region	ns of c	peratio	n? Ho	w can	they be der	narca	ated in the	figuration. What are the output characteristics?	
	b) Exp	lain the	curre	nt com	ponen	ts of E	3JT and deri	ive a i	relation be	tween α and β.	
14.	a) Deri	ive vol	age ga	ain and	currer	nt gain	for CE BJ7	Γ amp	plifier usin	g h-parameter model.	
	b) Exp	lain the	work	ing of	a DIA	C and	compare it	with a	a TRIAC.		
15.	a) Dra	w and	explain	n the cl	naracte	ristics	of a JFET.				
			_				and operation		a depletion	MOSFET.	
16	a) Wri	te a sho	ort not	e on Z	ener vo	ltage	regulator ar	nd its	limitation	S.	
20.	,					_	g diode and				
17.	. Answer	any tv	of t	he follo	wing:						
	a) S	Stabilit	y facto	r of BJ	T.						
	-	Write s									
	·c) I	List and	expla	in FE1	appli	cation	is.				